TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

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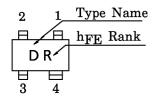
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

- Low Noise Figure, High Gain.
- NF=1.8dB, $|S_{21e}|^2$ =9.5dB (f=2GHz)

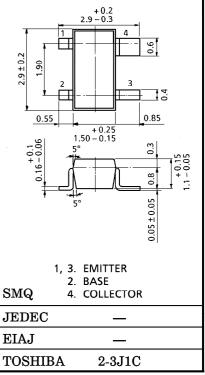
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	20	V
Collector-Emitter Voltage	v_{CEO}	10	V
Emitter-Base Voltage	$V_{ m EBO}$	1.5	V
Base Current	$I_{\mathbf{B}}$	20	mA
Collector Current	$^{\mathrm{I}}\mathrm{C}$	40	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	150	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

MARKING



Unit in mm



Weight: 0.012g

MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Transition Frequency	$ m f_T$	$V_{CE}=8V, I_{C}=20mA$	7	10	_	GHz	
Insertion Gain	$ S_{21e} ^2$ (1)	V_{CE} =8V, I_{C} =20mA, f=1GHz	12	15	_	dB	
	$ S_{21e} ^2$ (2)	V_{CE} =8V, I_{C} =20mA, f =2GHz	6.5	9.5	_	ub	
Noise Figure	NF (1)	$V_{CE}=8V$, $I_{C}=5mA$, $f=1GHz$	_	1.4	2.5	dB	
	NF (2)	$V_{CE}=8V$, $I_{C}=5mA$, $f=2GHz$	_	1.8	3	иБ	

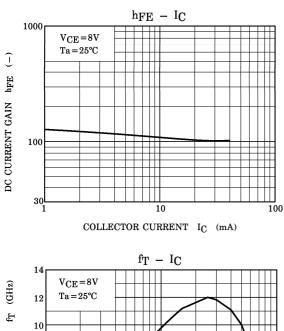
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

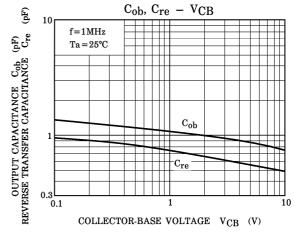
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 10V, I_{E} = 0$	_	_	1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=1V, I_{C}=0$	_	_	1	μ A
DC Current Gain	hFE (Note 1)	$V_{CE}=8V, I_{C}=20mA$	50	_	160	_
Output Capacitance	$C_{f ob}$	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		0.7	1.1	рF
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	(Note 2)	_	0.45	0.95	pF

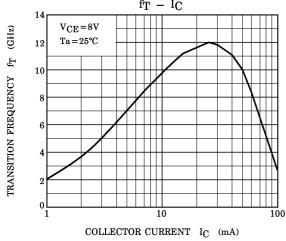
(Note 1) hFE Classification $R:50\sim100$, $O:80\sim160$

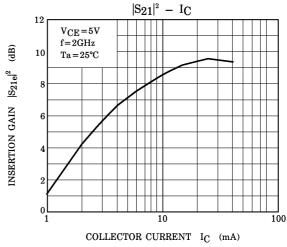
(Note 2) Cre is measured by 3 terminal method with capacitance bridge.

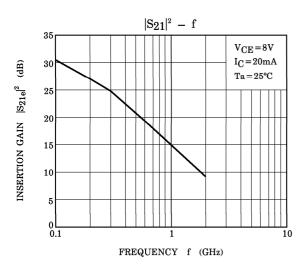
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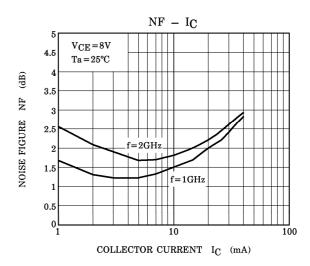


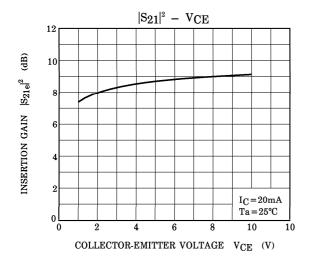


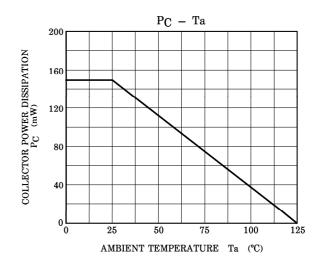












S-Parameter $Z_O = 50\Omega$, $T_0 = 25^{\circ}C$ $V_{CE} = 8V$, $I_C = 5mA$

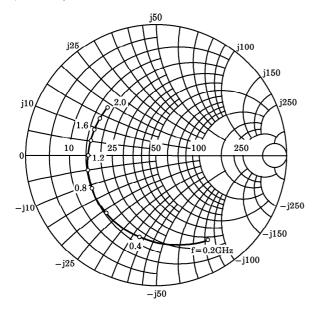
frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.767	-58.9	12.888	143.5	0.049	62.8	0.856	-34.5
400	0.655	-102.2	9.480	119.3	0.073	48.7	0.663	-57.5
600	0.605	-130.0	7.087	104.6	0.086	43.1	0.535	-72.7
800	0.567	-150.4	5.577	93.9	0.093	40.7	0.456	-84.3
1000	0.547	-166.4	4.548	86.0	0.098	41.1	0.407	-93.8
1200	0.533	-179.7	3.798	79.3	0.103	42.5	0.373	-102.4
1400	0.528	169.1	3.268	76.9	0.109	44.1	0.346	-110.3
1600	0.519	158.4	2.856	69.3	0.116	46.6	0.328	-117.4
1800	0.520	148.3	2.551	65.1	0.124	48.9	0.314	-123.0
2000	0.524	138.7	2.290	61.1	0.133	51.1	0.303	-128.3

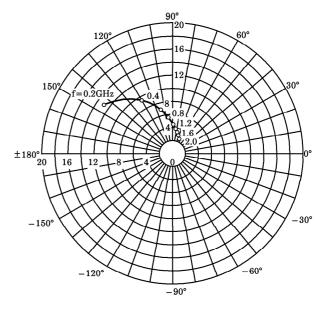
 $V_{CE} = 8V \setminus I_C = 20mA$

CL	_							
frequency	requency S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.540	-106.8	23.009	123.0	0.033	56.9	0.605	-57.8
400	0.521	-147.5	13.445	102.7	0.045	54.9	0.392	-81.2
600	0.521	-167.1	9.277	92.8	0.057	57.9	0.309	-95.5
800	0.525	-178.9	7.029	85.7	0.069	60.0	0.271	-107.3
1000	0.526	-168.8	5.651	80.0	0.082	62.5	0.250	-117.9
1200	0.529	-158.7	4.688	75.6	0.094	63.4	0.236	-127.6
1400	0.531	-148.5	4.011	71.6	0.106	64.5	0.225	-136.2
1600	0.536	-140.4	3.531	68.1	0.119	65.1	0.214	-143.8
1800	0.539	-131.7	3.159	64.7	0.133	65.5	0.201	-149.8
2000	0.540	-122.8	2.842	61.8	0.147	65.7	0.190	-154.8

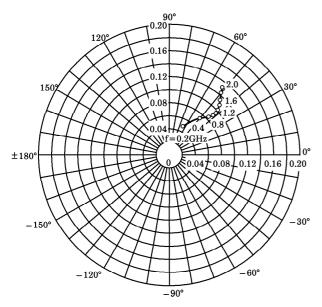
 $\begin{array}{l} S_{11e} \\ V_{CE} = 8V \\ I_{C} = 5 \text{mA} \\ Ta = 25 ^{\circ}\text{C} \\ \text{(Unit: } \Omega\text{)} \end{array}$

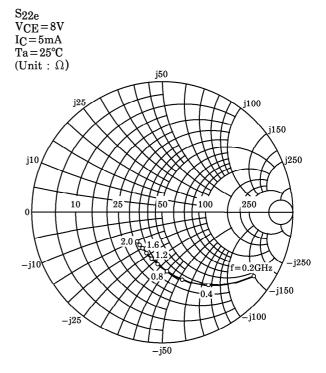






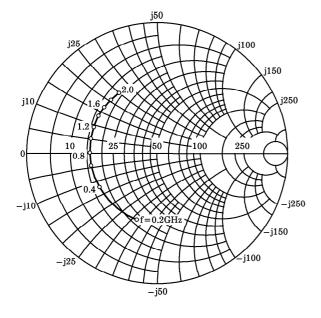
 $\begin{array}{c} S_{12e} \\ V_{CE} = 8V \\ I_{C} = 5 \text{mA} \\ Ta = 25 ^{\circ}\text{C} \end{array}$

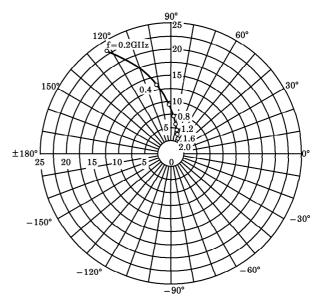




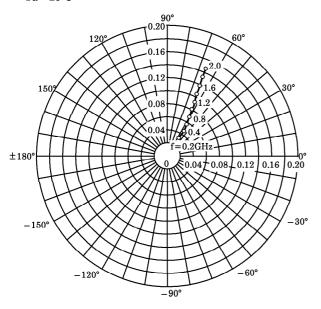
 $\begin{array}{l} S_{11e} \\ V_{CE} = 8V \\ I_{C} = 20 mA \\ Ta = 25 ^{\circ}C \\ (Unit: \Omega) \end{array}$

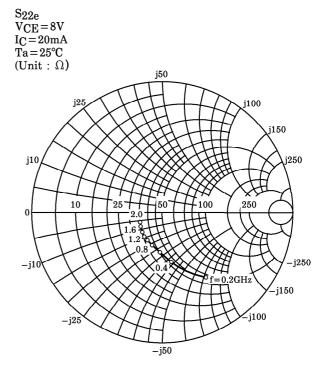






 $\begin{array}{l} \mathrm{S}_{12e} \\ \mathrm{V}_{CE} \!=\! 8\mathrm{V} \\ \mathrm{I}_{C} \!=\! 20\mathrm{mA} \\ \mathrm{Ta} \!=\! 25^{\circ}\!\mathrm{C} \end{array}$





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